

# SKM 150 MLI 066 T



**SEMITRANS<sup>®</sup> 5**

## Trench IGBT Modules

### SKM 150 MLI 066 T

#### Target Data

#### Features

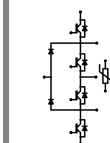
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$  with positive temperature coefficient
- Integrated NTC temperature sensor

#### Typical Applications\*

- UPS
- 3 Level Inverter

#### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max, recommended  $T_{op} = -40..+150^\circ\text{C}$



MLI-T

Absolute Maximum Ratings		$T_{case} = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	600		V
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	200	A
		$T_c = 80^\circ\text{C}$	150	A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	300		A
$V_{GES}$		$\pm 20$		V
$t_{psc}$	$V_{CC} = 360\text{ V}; V_{GE} \leq 15\text{ V}; T_j = 150^\circ\text{C}$ $V_{CES} < 600\text{ V}$	6		$\mu\text{s}$
<b>Inverse Diode</b>				
$I_F$	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	200	A
		$T_c = 80^\circ\text{C}$	145	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	300		A
$I_{FSM}$	$t_p = 10\text{ ms};$ half sine wave $T_j = 150^\circ\text{C}$	1080		A
<b>Freewheeling Diode</b>				
$I_F$	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	200	A
		$T_c = 80^\circ\text{C}$	145	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	300		A
$I_{FSM}$	$t_p = 10\text{ ms};$ half sine wave $T_j = 150^\circ\text{C}$	1080		A
<b>Module</b>				
$I_{t(RMS)}$		500		A
$T_{vj}$		- 40 ... + 175		$^\circ\text{C}$
$T_{stg}$		- 40 ... + 125		$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500		V

Characteristics		$T_{case} = 25^\circ\text{C}$ , unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
<b>IGBT</b>						
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2,4\text{ mA}$	5	5,8	6,5	V	
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$ $T_j = 25^\circ\text{C}$			0,0076	mA	
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$ $T_j = 25^\circ\text{C}$			600	nA	
$V_{CE0}$			$T_j = 25^\circ\text{C}$	0,9	1	V
			$T_j = 150^\circ\text{C}$	0,85	0,9	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	3,6	6	$\text{m}\Omega$	
		$T_j = 150^\circ\text{C}$	5,4	7,6	$\text{m}\Omega$	
$V_{CE(sat)}$	$I_{Cnom} = 150\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,45	1,9	V	
		$T_j = 150^\circ\text{C}_{chiplev.}$	1,7	2,1	V	
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$ $f = 1\text{ MHz}$		9,2		nF	
$C_{oes}$		0,57		nF		
$C_{res}$		0,27		nF		
$R_{Gint}$	$T_j = ^\circ\text{C}$	2		$\Omega$		
$t_{d(on)}$	$R_{Gon} = 2\ \Omega$	$V_{CC} = 300\text{ V}$ $I_C = 150\text{ A}$	0,7		ns	
$t_r$					ns	
$E_{on}$	$R_{Goff} = 4\ \Omega$	$T_j = 150^\circ\text{C}$ $V_{GE} = -8\text{ V}/+15\text{ V}$	4,7		mJ	
$t_{d(off)}$					ns	
$t_f$					ns	
$E_{off}$					mJ	
$R_{th(j-c)}$	per IGBT	0,29		K/W		



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### Typical Applications\*

- UPS
- 3 Level Inverter

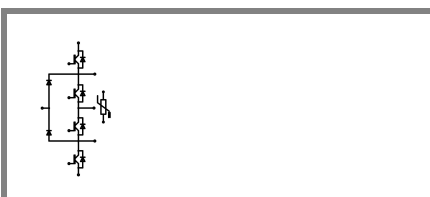
### Remarks

- Case temperature limited to  $T_C = 125^\circ\text{C}$  max, recommended  $T_{op} = -40..+150^\circ\text{C}$

Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 150\text{ A}; V_{GE} = 0\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,35	1,6	V
		$T_j = 150^\circ\text{C}_{chiplev.}$	1,35	1,6	V
$V_{F0}$		$T_j = 25^\circ\text{C}$	1	1,1	V
		$T_j = 150^\circ\text{C}$	0,9	1	V
$r_F$		$T_j = 25^\circ\text{C}$	2,3	3,3	mΩ
		$T_j = 150^\circ\text{C}$	3	4	mΩ
$I_{RRM}$	$I_F = 150\text{ A}$				A
$Q_{rr}$					μC
$E_{rr}$	$V_{GE} = -8\text{ V}; V_{CC} = 300\text{ V}$				mJ
$R_{th(j-c)D}$	per diode		0,52		K/W
<b>Free-wheeling diode (Neutral Clamp Diode)</b>					
$V_F = V_{EC}$	$I_{Fnom} = 150\text{ A}; V_{GE} = 0\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,35	1,6	V
		$T_j = 150^\circ\text{C}_{chiplev.}$	1,35	1,6	V
$V_{F0}$		$T_j = 25^\circ\text{C}$	1	1,1	V
		$T_j = 150^\circ\text{C}$	0,9	1	V
$r_F$		$T_j = 25^\circ\text{C}$	2,3	3,3	V
		$T_j = 150^\circ\text{C}$	3	4	V
$I_{RRM}$	$I_F = 150\text{ A}$				A
$Q_{rr}$					μC
$E_{rr}$	$V_{GE} = 0\text{ V}; V_{CC} = 600\text{ V}$				mJ
$R_{th(j-c)FD}$	per diode		0,52		K/W
$R_{th(c-s)}$	per module			0,038	K/W
$M_s$	to heat sink M6	3		5	Nm
$M_t$	to terminals M6	2,5		5	Nm
w				310	g
<b>Temperature sensor</b>					
$R_{100}$	$T_s = 100^\circ\text{C}$ ( $R_{25} = 5\text{ k}\Omega$ )		493±5%		Ω K

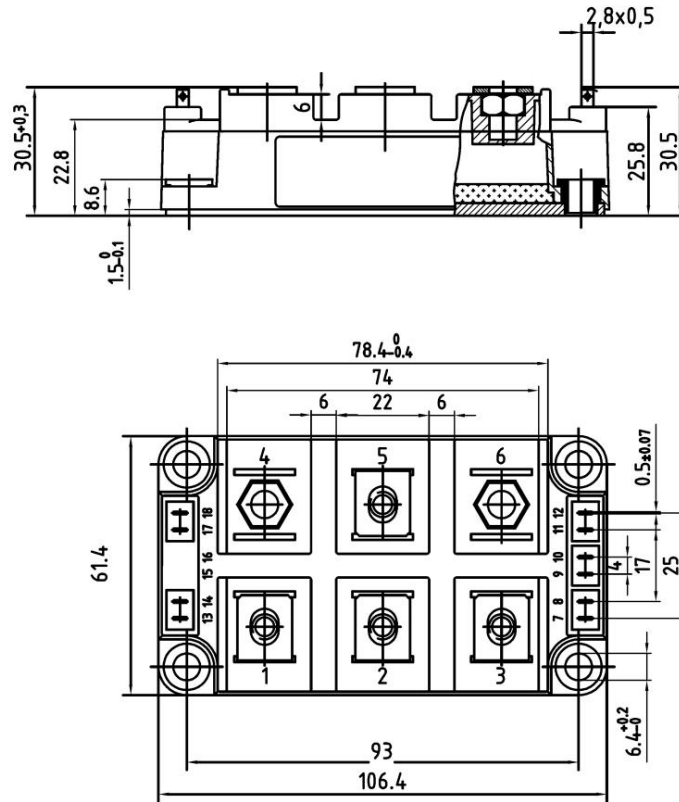
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

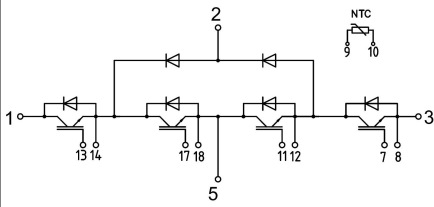


**MLI-T**

# SKM 150 MLI 066 T



Case D60



MLI-T

Case D60